

**TRANSISTOR (PNP)**
**Plastic-Encapsulate Transistor**
**FEATURES**

Power dissipation

$$P_{CM} : 0.5W (T_{amb}=25^{\circ}C)$$

Collector current

$$I_{CM} : -1.5A$$

Collector-base Voltage

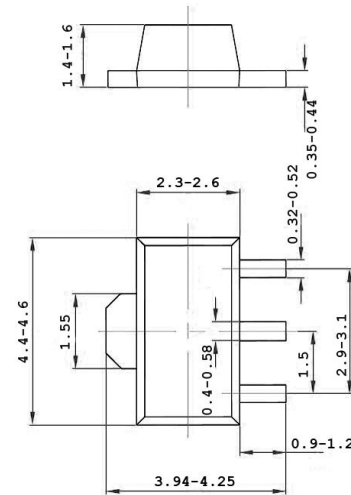
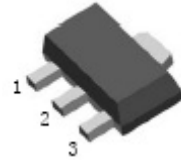
$$V_{(BR)CBO} : -35 V$$

Operating and storage junction temperature range

$$T_J, T_{stg} : -55^{\circ}C \text{ to } +150^{\circ}C$$

**MARKING : HO ,HY**
**SOT-89**

1. BASE
2. COLLECTOR(HEAT SINK)
3. EMITTER



UNIT:mm

**MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS**

Ratings at 25°C ambient temperature unless otherwise specified.

**ELECTRICAL CHARACTERISTICS**

Parameters	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-1mA, I_E=0$	-35			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-30			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-1mA, I_C=0$	-5			V
Collector Cut-Off Current	$I_{CBO}$	$V_{CB}=-30V, I_E=0$			-0.1	$\mu A$
Emitter Cut-Off Current	$I_{EBO}$	$V_{EB}=-5V, I_C=0$			-0.1	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE}=-2V, I_C=-500mA$	100		320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-1.5A, I_B=-30mA$			-2.0	V
Base-Emitter Saturation Voltage	$V_{BE}$	$V_{CE}=-2V, I_C=500mA$			-1.0	
Transition Frequency	$f_T$	$V_{CE}=-5V, I_C=-50mA$	80			MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=-10V, I_E=0, f=1MHz$			50	pF

**CLASSIFICATION OF  $h_{FE}$** 

Rank	O	Y
Range	100-200	160-320

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